

ABSTRACT OF THE DISCLOSURE

There is provided a resist pattern forming method which makes it possible to form fine resist patterns with a high aspect ratio by using a non-chemically amplified resist easy to treat. In the resist pattern forming method, a resist layer is formed on a substrate by applying a non-chemically amplified resist onto the substrate. Then, the resist layer is exposed. Thereafter, the substrate subjected to the exposure is baked at a temperature not lower than 90°C but not higher than 130°C, and the baked substrate is developed.